

Features

 $BV_{CEO} > 60V$

I_C = 6A High Continuous Collector Current

Low Saturation Voltage V_{CE(SAT)} < 100mV @ 1A

h_{FE} Specified Up to 10A for a High Gain Hold Up

Lead-Free Finish; RoHS Compliant (Notes 1 & 2) Halogen and Antimony Free. "Green" Device (Note 3) Qualified to AEC-Q101 Standards for High Reliability

 $R_{CE(SAT)} = 44m\Omega$ for a Low Equivalent On-Resistance

I_{CM} = 20A Peak Pulse Current

PPAP Capable (Note 4)

Complementary PNP Type: FZT951



60V NPN MEDIUM POWER TRANSISTOR IN SOT223

Mechanical Data

- Case: SOT223
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads. Solderable per MIL-STD-202, Method 208 3
- Weight: 0.112 grams (Approximate)

Ordering Information (Notes 4 & 5)

Product	Compliance	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
FZT851TA	AEC-Q101	FZT851	7	12	1,000
FZT851QTA	Automotive	FZT851	7	12	1,000

1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied. 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green"

and Lead-free

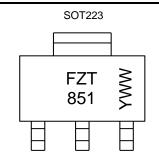
Notes:

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified. For more information, please refer to http://www.diodes.com/quality/product_compliance_definitions/.

5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



FZT 851 = Product Type Marking Code YWW = Date Code Marking Y or \overline{Y} = Last Digit of Year (ex: 5= 2015) WW or $\overline{W}W$ = Week Code (01–53)



Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	150	V
Collector-Emitter Voltage	V _{CEO}	60	V
Emitter-Base Voltage	V _{EBO}	7	V
Continuous Collector Current	lc	6	A
Peak Pulse Current	I _{CM}	20	A

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Power Dissipation	(Note 6)	6	3.0 24	W	
Linear Derating Factor	(Note 7)	PD	1.6 12.8	mW/°C	
Thermal Desistance, Junction to Ambient	(Note 6)	R _{θJA}	42		
Thermal Resistance, Junction to Ambient	(Note 7)	R _{θJA}	78	°C/W	
Thermal Resistance Junction to Lead	(Note 8)	R _{θJL}	8.8		
Operating and Storage Temperature Range		TJ, TSTG	-55 to +150	°C	

ESD Ratings (Note 9)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	8,000	V	3B
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

Notes: 6. For a device mounted with the collector lead on 52mm x 52mm 2oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in steady-state.

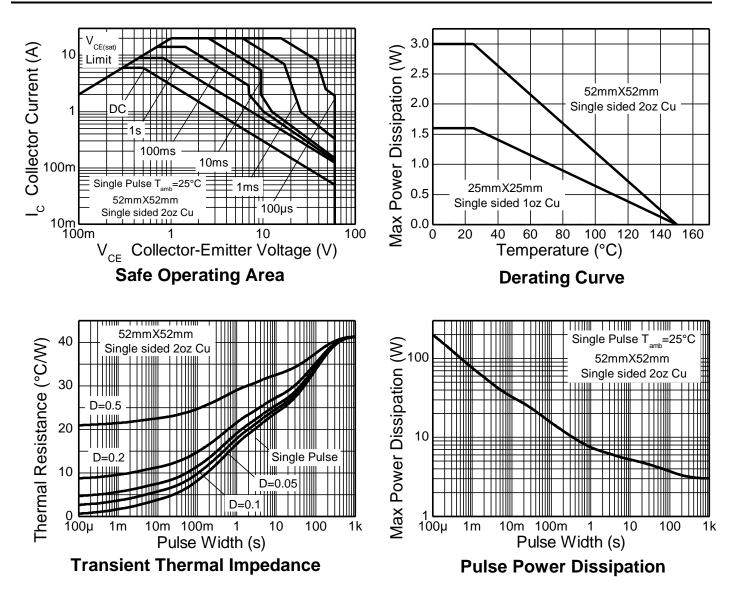
7. Same as Note 6, except the device is mounted on 25mm x 25mm 1oz copper.

8. Thermal resistance from junction to solder-point (at the end of the collector lead).

9. Refer to JEDEC specification JESD22-A114 and JESD22-A115.



Thermal Characteristics and Derating Information





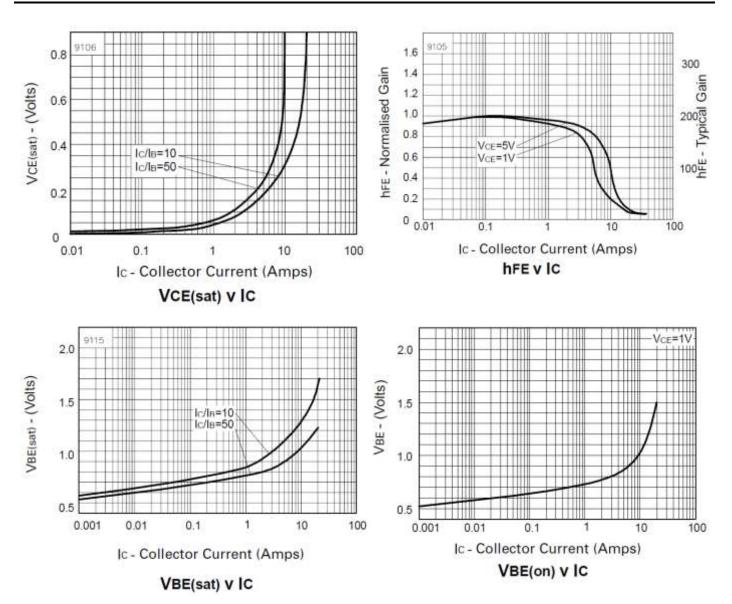
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	150	220	_	V	$I_{\rm C} = 100\mu A$
Collector-Emitter Breakdown Voltage	BV _{CER}	150	220		V	$I_{\rm C} = 1\mu A, R_{\rm B} \le 1k\Omega$
Collector-Emitter Breakdown Voltage (Note 10)	BVCEO	60	85		V	$I_{\rm C} = 10 {\rm mA}$
Emitter-Base Breakdown Voltage	BV _{EBO}	7	8.1		V	I _E = 100μA
Collector Cut-Off Current		_	<1	50	nA	V _{CB} = 120V
	I _{CBO}		-	1	μA	V _{CB} = 120V, T _A = +100°C
Collector Cut-Off Current	ICER	_	<1	50	nA	$V_{CE} = 120V, R_B \le 1k\Omega$
	ICER		—	1	μA	$V_{CE} = 120V, T_A = +100^{\circ}C$
Emitter Cut-Off Current	I _{EBO}	—	<1	10	nA	$V_{EB} = 6V$
		100	200	_		$I_{C} = 10 \text{mA}, V_{CE} = 1 \text{V}$
DC Current Gain (Note 10)	h _{FE}	100	200	300		$I_C = 2A, V_{CE} = 1V$
		75	120	_		$I_C = 5A, V_{CE} = 1V$
		25	50	_		I _C = 10A, V _{CE} = 1V
	V _{CE(SAT)}	_	_	50	mV	$I_{\rm C} = 100 {\rm mA}, I_{\rm B} = 5 {\rm mA}$
Callester Emitter Caturation Materia (Nate 40)			_	100		$I_{\rm C} = 1$ A, $I_{\rm B} = 50$ mA
Collector-Emitter Saturation Voltage (Note 10)			_	170		$I_{\rm C} = 2A, I_{\rm B} = 50 {\rm mA}$
			_	375		$I_{\rm C} = 6A, I_{\rm B} = 300 {\rm mA}$
Base-Emitter Saturation Voltage (Note 10)	V _{BE(SAT)}	_	_	1,200	mV	$I_{\rm C} = 6A, I_{\rm B} = 300 {\rm mA}$
Base-Emitter Turn-On Voltage (Note 10)	V _{BE(ON)}	_	_	1,150	mV	$I_{C} = 6A, V_{CE} = 1V$
Current Gain-Bandwidth Product (Note 10)	fT	_	130	_	MHz	$I_{C} = 100 \text{mA}, V_{CE} = 10 \text{V},$ f = 50 MHz
Output Capacitance	COBO	—	45	—	pF	$V_{CB} = 10V$, f = 1MHz
Switching Times	t _{ON}	_	45	_	nc	$I_{C} = 1A, V_{CC} = 10V,$
	tOFF	_	1,100	_	ns	$I_{B1} = -I_{B2} = 100 \text{mA}$

Note: 10. Measured under pulsed conditions. Pulse width \leq 300µs. Duty cycle \leq 2%.



Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

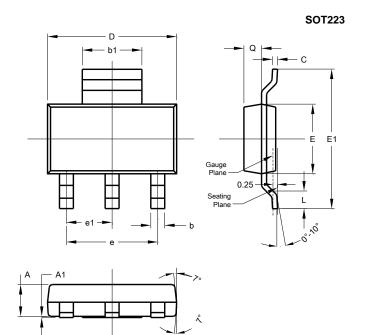


FZT851



Package Outline Dimensions

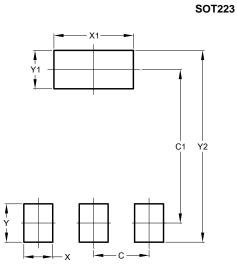
Please see http://www.diodes.com/package-outlines.html for the latest version.



SOT223						
Dim	Min	Max	Тур			
Α	1.55	1.65	1.60			
A1	0.010	0.15	0.05			
b	0.60	0.80	0.70			
b1	2.90	3.10	3.00			
С	0.20	0.30	0.25			
D	6.45	6.55	6.50			
Е	3.45	3.55	3.50			
E1	6.90	7.10	7.00			
е	-	-	4.60			
e1	-	-	2.30			
L	0.85	1.05	0.95			
Q	0.84	0.94	0.89			
All [All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



Dimensions	Value (in mm)
С	2.30
C1	6.40
Х	1.20
X1	3.30
Y	1.60
Y1	1.60
Y2	8.00



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